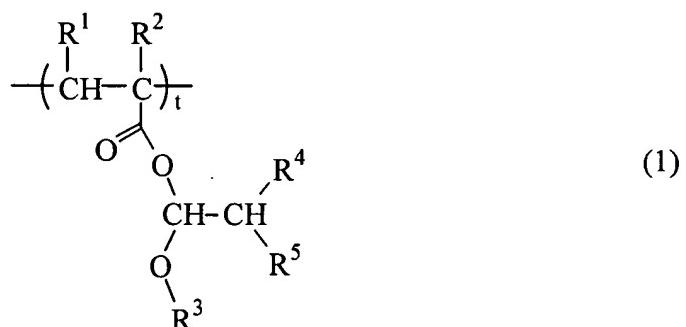


## AMENDMENTS TO THE CLAIMS

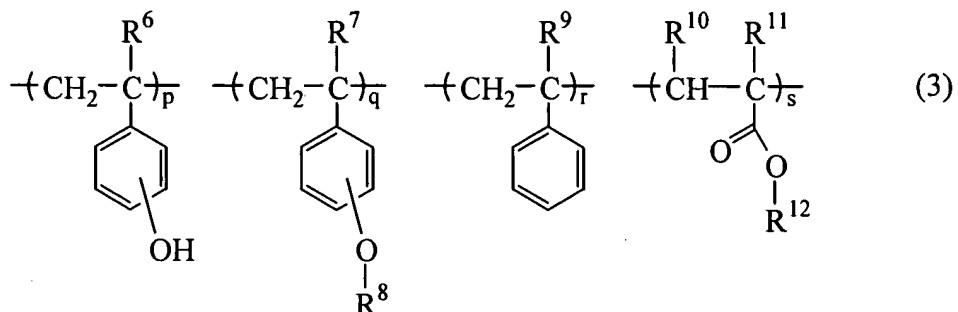
1. (Cancelled)

2. (Cancelled)

3. (Original) A resist composition comprising a polymer comprising recurring units of the following general formula (1) and recurring units of the following general formula (3) and having a weight average molecular weight of 1,000 to 500,000,

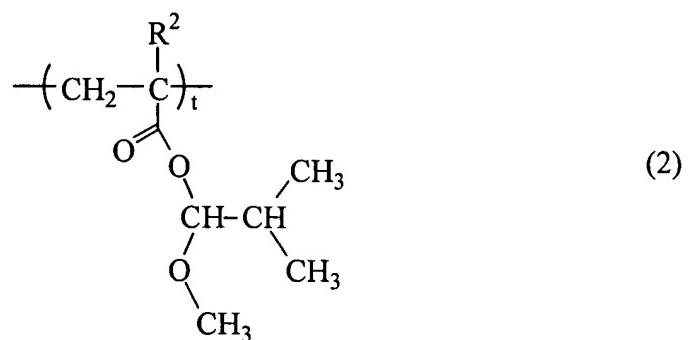


wherein R<sup>1</sup> and R<sup>2</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>3</sup> is methyl or ethyl, R<sup>4</sup> and R<sup>5</sup> each are an alkyl group having 1 to 7 carbon atoms, or R<sup>4</sup> and R<sup>5</sup> may bond together to form a cyclic structure, t is a positive number,

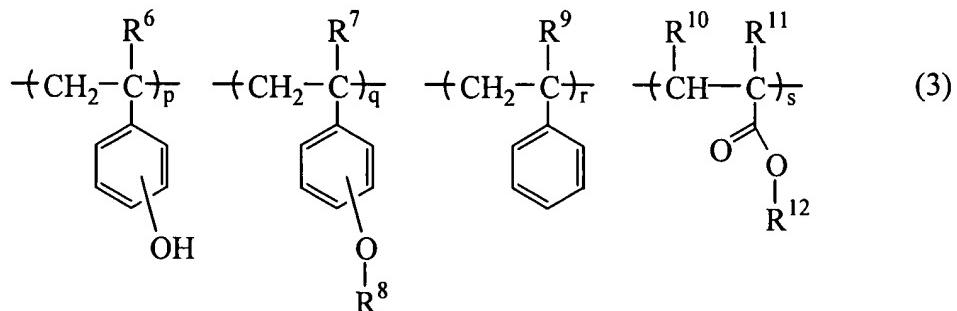


wherein R<sup>6</sup>, R<sup>7</sup>, R<sup>9</sup>, R<sup>10</sup> and R<sup>11</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>8</sup> is an alkyl group having 1 to 10 carbon atoms, R<sup>12</sup> is an alkyl group having 4 to 30 carbon atoms or silicon-substituted alkyl group, q, r and s are 0 or positive numbers, and p is a positive number.

4. (Original) A resist composition comprising a polymer comprising recurring units of the following general formula (2) and recurring units of the following general formula (3) and having a weight average molecular weight of 1,000 to 500,000,



wherein R<sup>2</sup> is hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, and t is a positive number,



wherein R<sup>6</sup>, R<sup>7</sup>, R<sup>9</sup>, R<sup>10</sup> and R<sup>11</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>8</sup> is an alkyl group having 1 to 10 carbon atoms, R<sup>12</sup> is an alkyl group having 4 to 30 carbon atoms or silicon-substituted alkyl group, q, r and s are 0 or positive numbers, and p is a positive number.

5. (Currently Amended) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 4 as a base resin, and
- (C) a photoacid generator.

6. (Currently Amended) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 1 as a base resin,
- (C) a photoacid generator, and
- (D) a dissolution inhibitor.

7. (Original) The chemically amplified positive resist composition of claim 5, further comprising (E) a basic compound.

8. (Currently Amended) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 1 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

9. (New) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 4 as a base resin, and
- (C) a photoacid generator.

10. (New) A chemically amplified positive resist composition comprising

- (A) an organic solvent,
- (B) the polymer of claim 4 as a base resin,
- (C) a photoacid generator, and
- (D) a dissolution inhibitor.

11. (New) The chemically amplified positive resist composition of claim 9, further comprising (E) a basic compound.

12. (New) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 9 onto a substrate to form a coating,

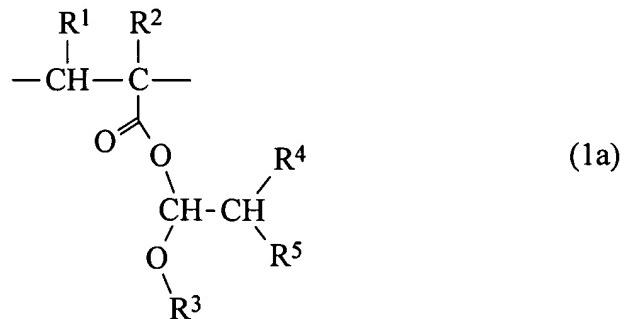
heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

13. (New) A chemically amplified positive resist composition comprising

- (A) an organic solvent,

(B) a polymer as a base resin comprising recurring units of the following general formula (1a) and having a weight average molecular weight of 1,000 to 500,000,



wherein R<sup>1</sup> and R<sup>2</sup> are each independently hydrogen, hydroxy, a straight or branched alkyl group, halogen atom or trifluoromethyl group, R<sup>3</sup> is methyl or ethyl, R<sup>4</sup> and R<sup>5</sup> each are an alkyl group having 1 to 7 carbon atoms, or R<sup>4</sup> and R<sup>5</sup> may bond together to form a cyclic structure,

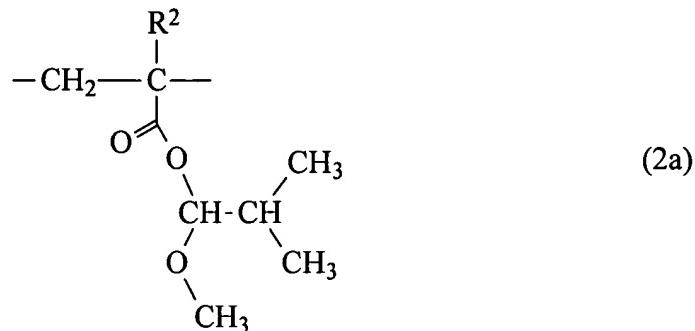
(C) a photoacid generator, and

(D) a basic compound.

14. (New) A chemically amplified positive resist composition comprising

(A) an organic solvent,

(B) a polymer as a base resin comprising recurring units of the following general formula (2a) and having a weight average molecular weight of 1,000 to 500,000,



wherein R<sup>2</sup> is a hydrogen, hydroxyl, a straight or branched alkyl group, halogen atom or trifluoromethyl group,

- (C) a photoacid generator, and
- (D) a basic compound.

15. (New) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 13 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

16. (New) A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 14 onto a substrate to form a coating,

heat treating the coating and then exposing it to high-energy radiation or electron beam through a photo mask, and optionally heat treating the exposed coating and developing it with a developer.